



# QPA3503

## 3 W, 28 V, 3.4 – 3.6 GHz GaN PA Module

### Product Description

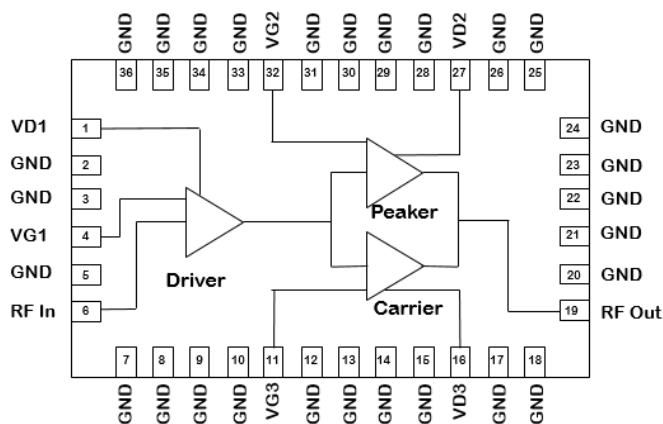
The QPA3503 is an integrated 2-stage Power Amplifier Module designed for massive MIMO applications with 3 W RMS at the device output covering frequency range from 3.4 to 3.6 GHz.

The module is 50  $\Omega$  input and output and requires minimal external components. The module is also compact and offers a much smaller footprint than traditional discrete component solutions.

The QPA3503 incorporates a Doherty final stage delivering high power added efficiency for the entire module at 3 W average power.

RoHS compliant.

### Functional Block Diagram



36 Pin 6x10 mm Plastic Package

### Product Features

- Operating Frequency Range: 3.4 - 3.6 GHz
- Operating Drain Voltage: +28 V
- 50  $\Omega$  Input / Output
- Integrated Doherty Final Stage
- Gain at 3 W avg.: 32 dB
- Power Added Efficiency at 3 W avg.: 33%
- 6x10 mm Plastic Surface Mount Package

### Applications

- 5G Massive MIMO
- W-CDMA / LTE
- Macrocell Base Station Driver
- Microcell Base Station
- Small Cell Final Stage
- Active Antenna
- General Purpose Applications

### Ordering Information

| Part No.     | Description             |
|--------------|-------------------------|
| QPA3503SB    | Sample Bag – 5 Pieces   |
| QPA3503SR    | Short Reel – 100 Pieces |
| QPA3503TR13  | 13" Reel – 2500 Pieces  |
| QPA3503EVB01 | Tested 3.4-3.6 GHz EVB  |



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### Absolute Maximum Ratings<sup>2</sup>

| Parameter                                                                              | Range / Value | Units              |
|----------------------------------------------------------------------------------------|---------------|--------------------|
| Breakdown Voltage, $BV_{DG}$                                                           | 120           | V                  |
| Gate Voltage ( $V_{G1,2,3}$ )                                                          | -7 to +2      | V                  |
| Drain Voltage ( $V_{D1,2,3}$ )                                                         | +40           | V                  |
| RF Input Power <sup>(1)</sup>                                                          | +25           | dBm                |
| VSWR Mismatch, P3dB Pulse (10 % duty cycle, 100 $\mu$ width), $T = 25^{\circ}\text{C}$ | 10:1          |                    |
| Storage Temperature                                                                    | -65 to +150   | $^{\circ}\text{C}$ |

1. Tested at 3.5 GHz,  $T = +25^{\circ}\text{C}$ , single-carrier, 20 MHz LTE signal with 7.8 dB PAR @ 0.01% CCDF.

2. Operation of this device outside the parameter ranges given above may cause permanent damage.

### Recommended Operating Conditions

| Parameter                       | Min | Typ  | Max | Units |
|---------------------------------|-----|------|-----|-------|
| Gate Voltage ( $V_{G1}$ )       |     | -2.6 |     | V     |
| Gate Voltage ( $V_{G2}$ )       |     | -4.5 |     | V     |
| Gate Voltage ( $V_{G3}$ )       |     | -2.6 |     | V     |
| Drain Voltage ( $V_{D1,2,3}$ )  |     | +28  |     | V     |
| Quiescent Current ( $I_{DQ1}$ ) |     | 50   |     | mA    |
| Quiescent Current ( $I_{DQ3}$ ) |     | 75   |     | mA    |

Electrical performance is measured under conditions noted in the electrical specifications table. Specifications are not guaranteed over all recommended operating conditions.

### Electrical Specifications

| Parameter                 | Conditions           | Min | Typ | Max | Units |
|---------------------------|----------------------|-----|-----|-----|-------|
| Frequency Range           |                      | 3.4 |     | 3.6 | GHz   |
| Driver Quiescent Current  |                      |     | 50  |     | mA    |
| Carrier Quiescent Current |                      |     | 75  |     | mA    |
| Gain                      | $P_{AVG} = 34.8$ dBm |     | 32  |     | dB    |
| P3dB                      | 3 dB PAR compression |     | 44  |     | dBm   |
| Power Added Efficiency    | $P_{AVG} = 34.8$ dBm |     | 33  |     | %     |
| Raw ACLR                  | $P_{AVG} = 34.8$ dBm |     | -28 |     | dBc   |

Test conditions unless otherwise noted:  $V_{D1,2,3} = +28$  V,  $I_{DQ1} = 50$  mA,  $I_{DQ3} = 75$  mA,  $V_{G2} = -4.5$  V,  $T = +25^{\circ}\text{C}$ , single-carrier, 20 MHz LTE signal with 7.8 dB PAR @ 0.01% CCDF, de-embedded from EVB measurements.

### Thermal and Reliability Information

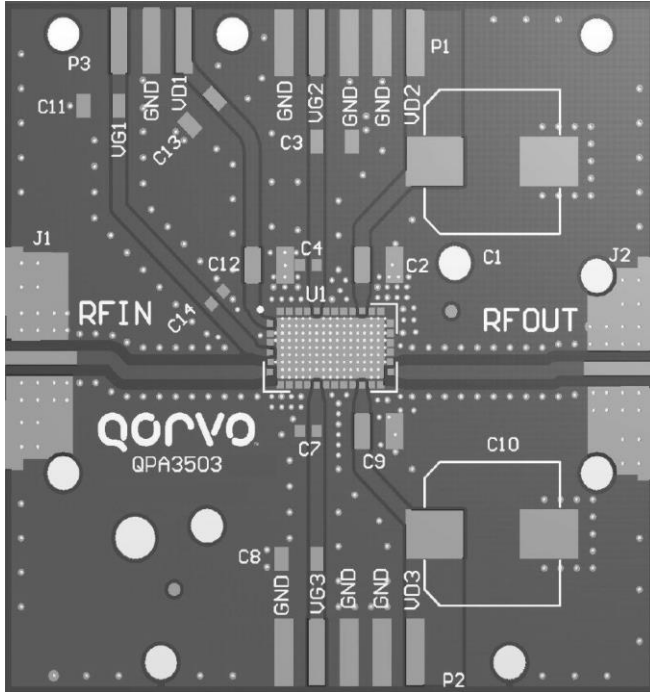
| Parameter                                                             | Test Conditions                                                                                              | Value | Units                |
|-----------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------|-------|----------------------|
| Peak IR Surface Thermal Resistance at Average Power ( $\theta_{JC}$ ) | $T_{CASE} = +85^{\circ}\text{C}$ , $T_{CH} = 101^{\circ}\text{C}$<br>CW: $P_{DISS} = 6.1$ W, $P_{OUT} = 3$ W | 2.6   | $^{\circ}\text{C/W}$ |

Notes:

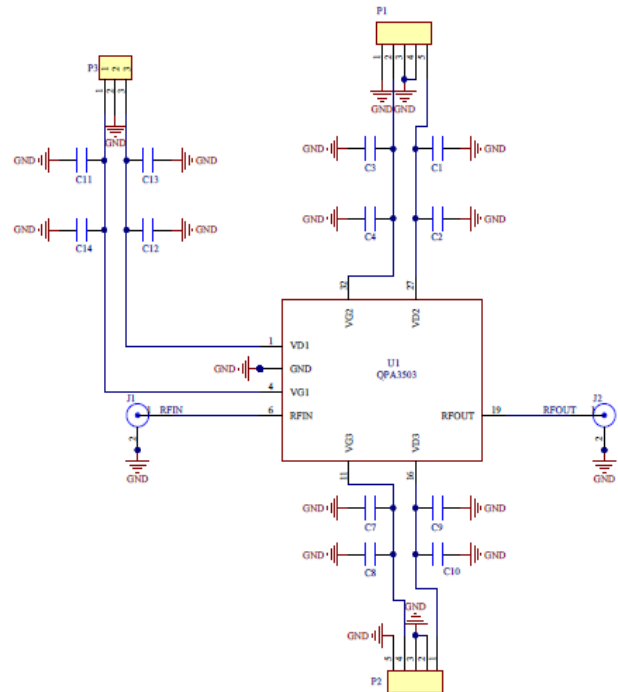
1. Thermal resistance measured to package backside.
2. Based on expected carrier amplifier efficiency of Doherty.
3.  $P_{OUT}$  assumes 20% peaking amplifier contribution of total average Doherty rated power.
4. Refer to the following document: [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)

### QPA3503 3.4 – 3.6 GHz Reference Design

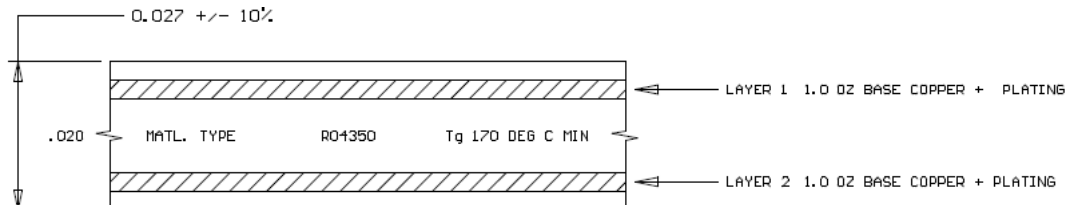
EVB Layout



EVB Schematic



PCB Stackup and Material



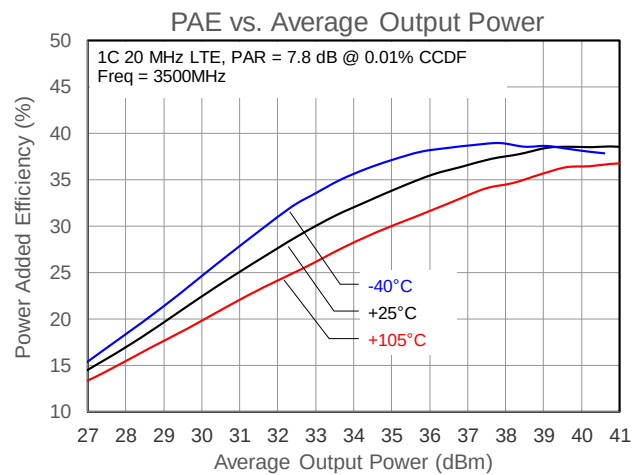
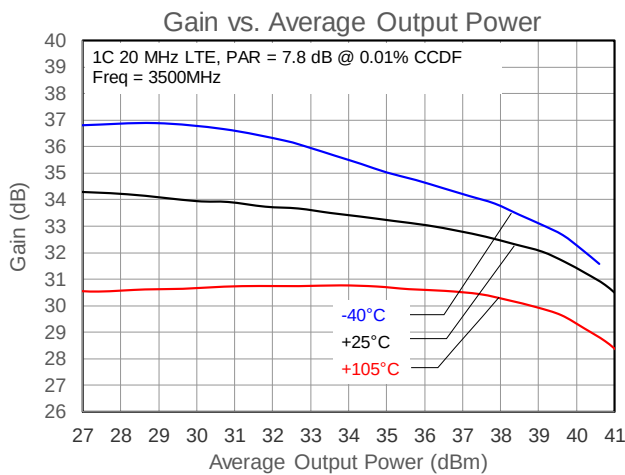
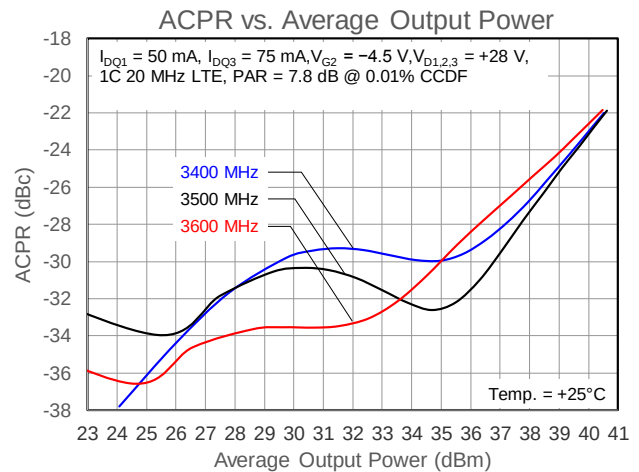
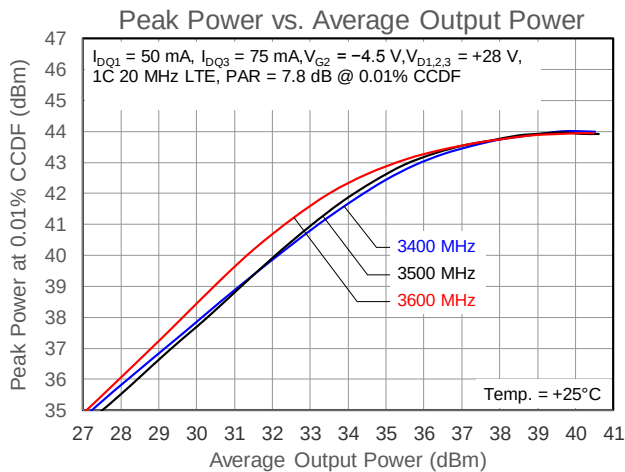
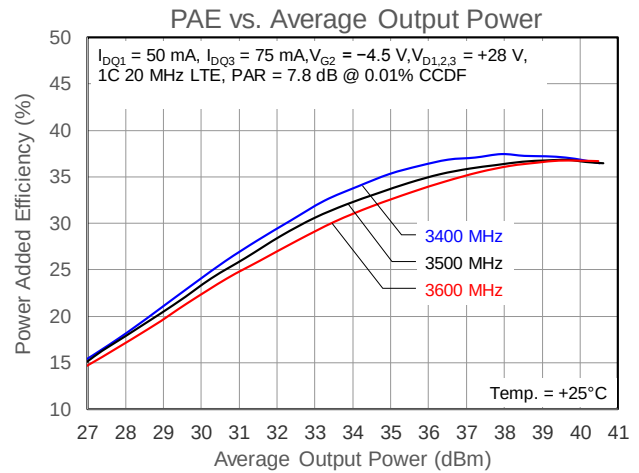
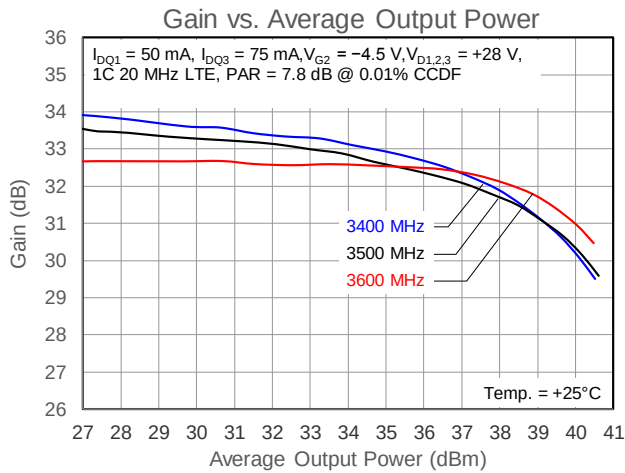
Notes:

1. All dimensions are in inches.
2. PCB is soldered on a 2 inch by 2 inch copper base plate with 0.25 inch thickness.

### Bill of Materials – QPA3503 3.5 GHz Evaluation Board

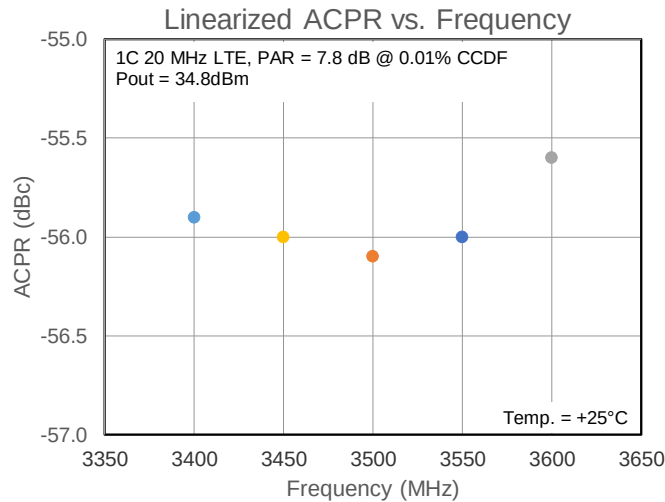
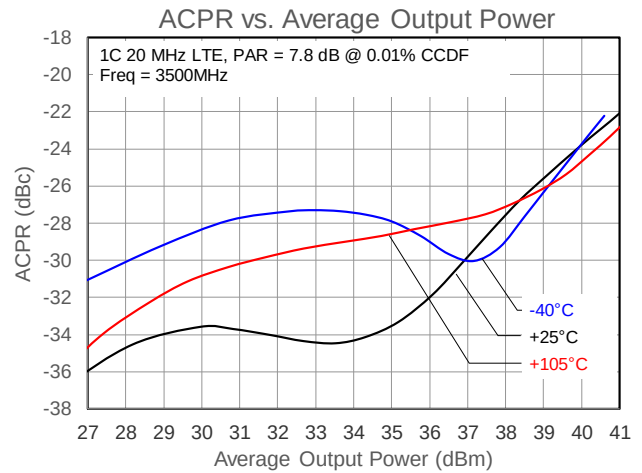
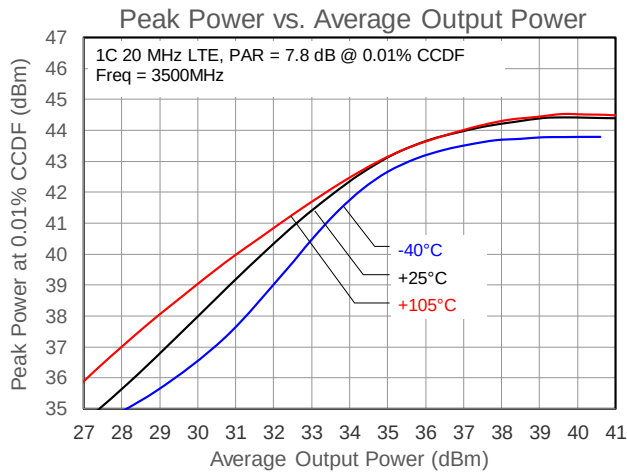
| Reference Des.   | Value       | Description                                  | Manuf.     | Part No.           |
|------------------|-------------|----------------------------------------------|------------|--------------------|
| C1, C10          | 220 $\mu$ F | Capacitor, 220 $\mu$ F, electrolytic 50 V    | Panasonic  | EEEFK1H221P        |
| C4, C7, C14      | 22,000 pF   | Capacitor, 22,000 pF, 10%, 50 V, X7R, 0603   | Murata     | GRM188R71H223KA01D |
| C3, C8, C11, C13 | 4.7 $\mu$ F | Capacitor, 4.7 $\mu$ F, 10%, 50 V, X7R, 1206 | Murata     | GRM31CR71H475KA12L |
| C2, C9, C12      | 10 $\mu$ F  | Capacitor, 10 $\mu$ F, 10%, 50 V, X7R, 1210  | Murata     | GRM32ER71H106KA    |
| J1, J2           |             | Connector, SMA, 4-Hole Panel Mount Jack      | Gigalane   | PAF-S00-000        |
| P1, P2           |             | Connector, HDR, ST, PLRZD, 5-Pin, 0.100"     | ITW Pancon | MPSS100-5-C        |
| P3               |             | Connector, HDR, ST, 3-PIN, T/H               | Molex      | 22-28-4033         |
| U1               |             | 3W 3.5GHz PA Module                          | Qorvo      | QPA3503            |

### Performance Plots



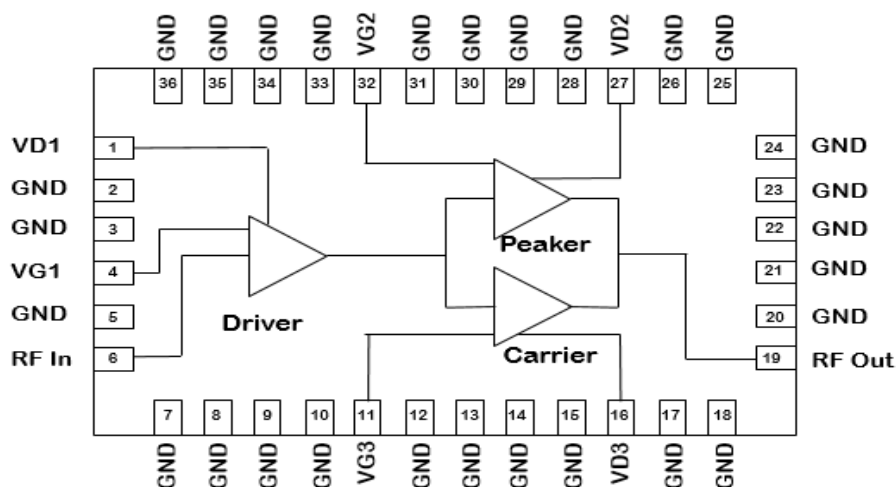
Test conditions unless otherwise noted:  $V_{D1,2,3} = +28 \text{ V}$ ,  $I_{DQ1} = 50 \text{ mA}$ ,  $I_{DQ3} = 75 \text{ mA}$ ,  $V_{G2} = -4.5 \text{ V}$ ,  $T = +25^\circ\text{C}$ , single-carrier, 20 MHz LTE signal with 7.8 dB PAR @ 0.01% CCDF, de-embedded from EVB measurements.

## Performance Plots



Test conditions unless otherwise noted:  $V_{D1,2,3} = +28\text{ V}$ ,  $I_{DQ1} = 50\text{ mA}$ ,  $I_{DQ3} = 75\text{ mA}$ ,  $V_{G2} = -4.5\text{ V}$ ,  $T = +25^\circ\text{C}$ , single-carrier, 20 MHz LTE signal with 7.8 dB PAR @ 0.01% CCDF, de-embedded from EVB measurements.

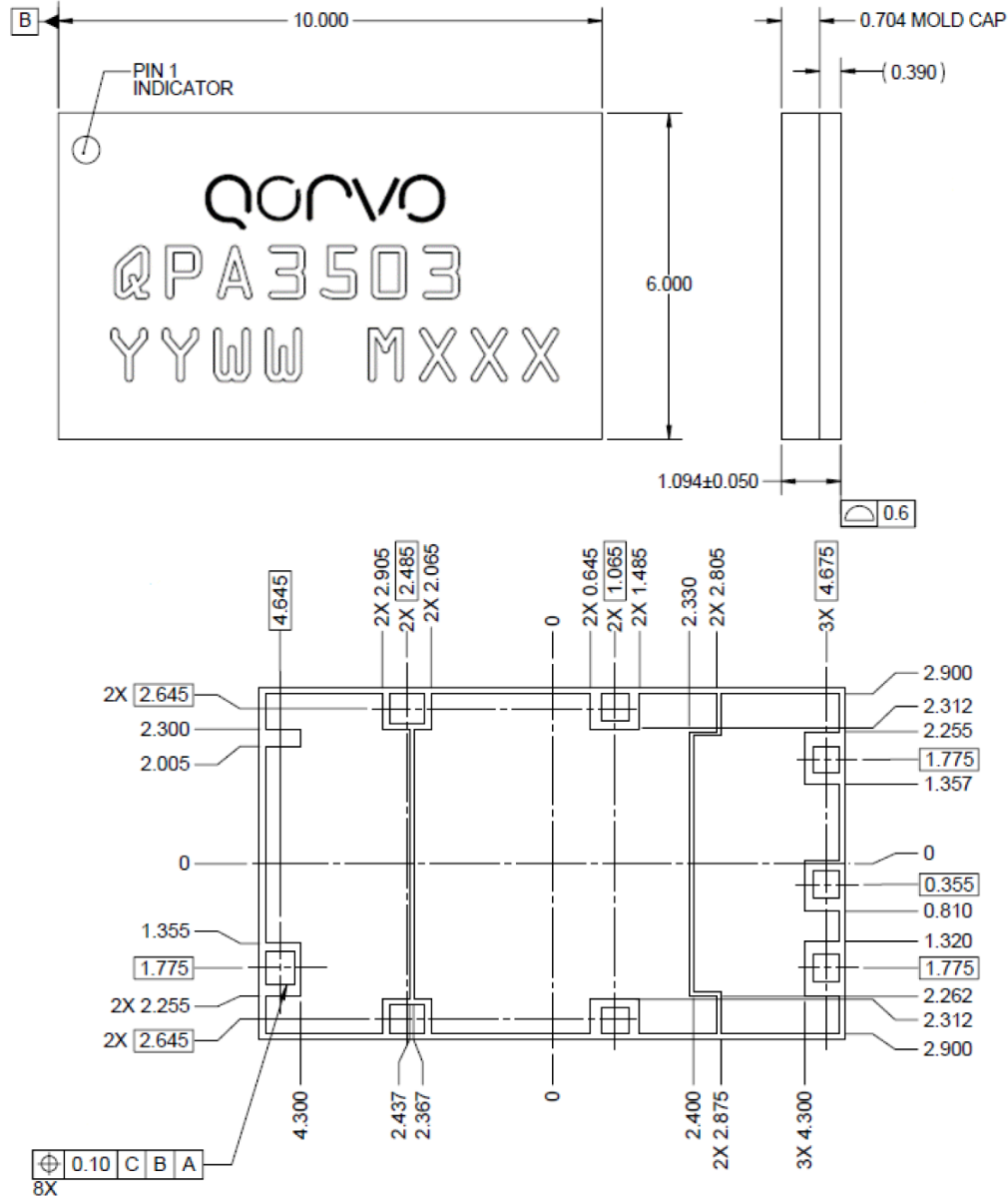
## Pin Configuration and Description



| Pin No.                                         | Label  | Description                                                                                                                                                                                            |
|-------------------------------------------------|--------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 1                                               | VD1    | Driver Amplifier, Drain Bias                                                                                                                                                                           |
| 4                                               | VG1    | Driver Amplifier, Gate Bias                                                                                                                                                                            |
| 6                                               | RF IN  | RF Input                                                                                                                                                                                               |
| 11                                              | VG3    | Carrier Amplifier, Gate Bias                                                                                                                                                                           |
| 16                                              | VD3    | Carrier Amplifier, Drain Bias                                                                                                                                                                          |
| 19                                              | RF OUT | RF Output                                                                                                                                                                                              |
| 27                                              | VD2    | Peaking Amplifier, Drain Bias                                                                                                                                                                          |
| 32                                              | VG2    | Peaking Amplifier, Gate Bias                                                                                                                                                                           |
| 2-3, 5, 7-10, 12-15, 17-18, 20-26, 28-31, 33-36 | GND    | Internal Grounding, recommend connecting to Epad ground                                                                                                                                                |
| EPAD                                            | GND    | DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under EPAD will result in excessive junction temperatures causing permanent damage. |

## Package Marking and Dimensions

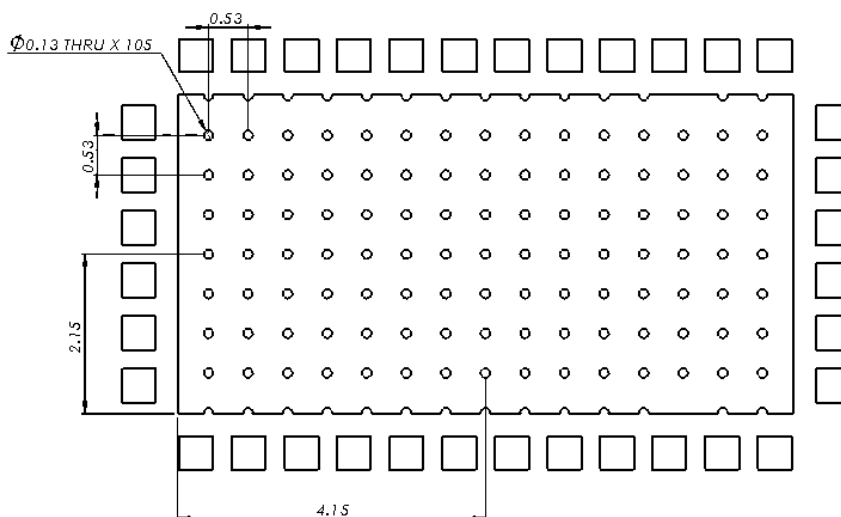
Marking: Qorvo Logo  
 Part Number – QPA3503  
 Date Code – YYWW  
 Batch Code – MXXX



### Notes:

- General tolerance is  $\pm 0.100$ .
- All dimensions are in mm. Angles are in degrees.
- Material:  
 Package Base: Laminate  
 Package Lid: Mold
- Exposed metallization is NiPdAu plated. Au thickness is 0.095  $\mu\text{m}$ .
- Part is mold sealed.

## Mounting Footprint Pattern

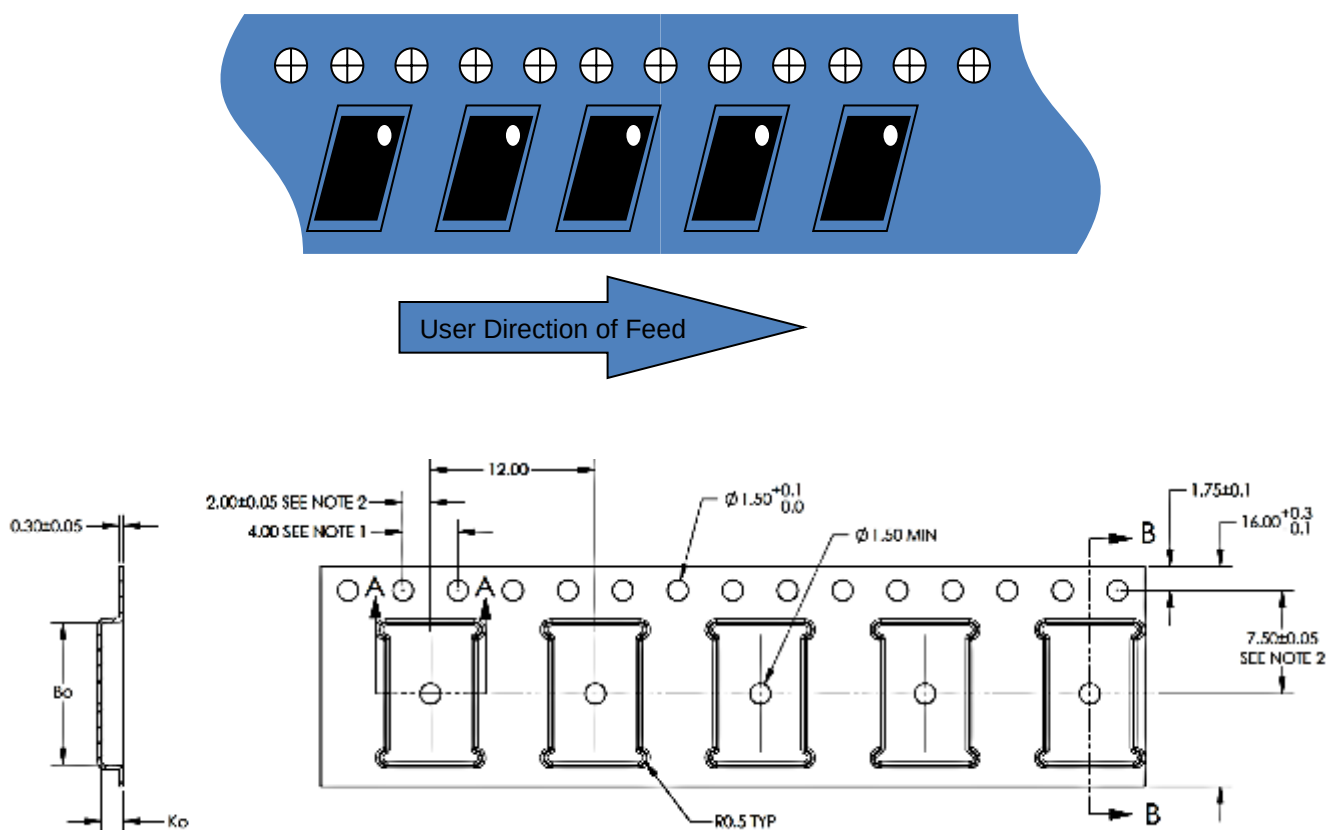


### Notes:

1. All dimensions are in mm. Angles are in degrees.
2. Vias are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. ALL vias are PTH to ground.
3. Ensure good package backside paddle solder attach for reliable operation and best electrical performance.



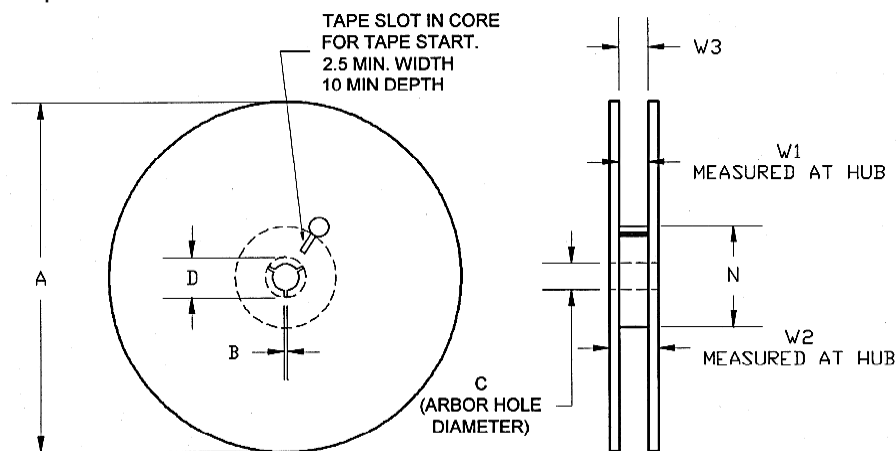
## Tape and Reel Information – Carrier and Cover Tape Dimensions



| Feature             | Measure                                  | Symbol | Size (in) | Size (mm) |
|---------------------|------------------------------------------|--------|-----------|-----------|
| Cavity              | Length                                   | A0     | 0.248     | 6.30      |
|                     | Width                                    | B0     | 0.406     | 10.3      |
|                     | Depth                                    | K0     | 0.061     | 1.55      |
|                     | Pitch                                    | P1     | 0.472     | 12.0      |
| Centerline Distance | Cavity to Perforation – Length Direction | P2     | 0.079     | 2.00      |
|                     | Cavity to Perforation – Width Direction  | F      | 0.295     | 7.5       |
| Cover Tape          | Width                                    | C      | 0.524     | 13.3      |
| Carrier Tape        | Width                                    | W      | 0.630     | 16.0      |

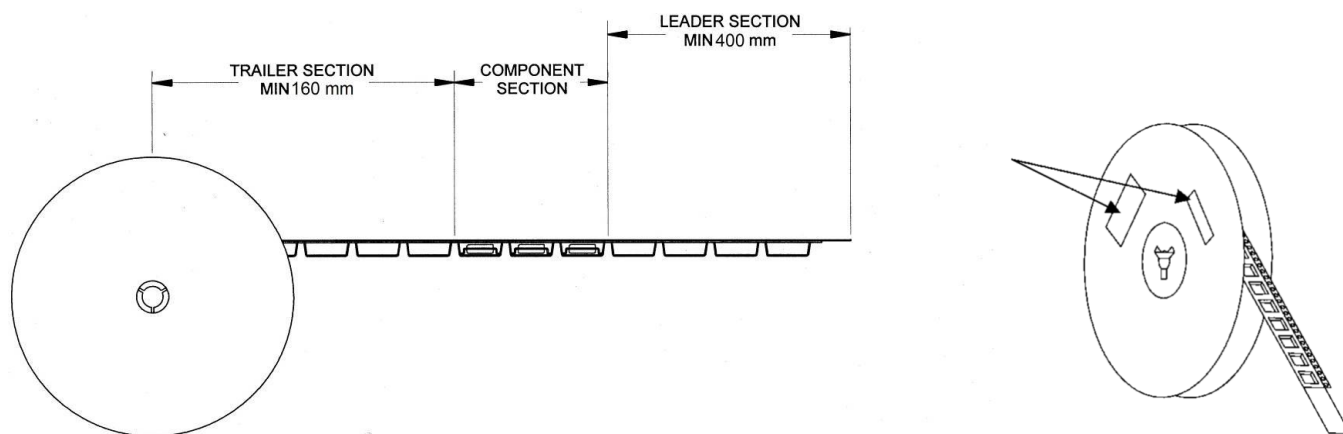
## Tape and Reel Information – Reel Dimensions

Standard T/R size = 2500 pieces on a 13" reel.



| Feature | Measure              | Symbol | Size (in) | Size (mm) |
|---------|----------------------|--------|-----------|-----------|
| Flange  | Diameter             | A      | 12.992    | 330.0     |
|         | Thickness            | W2     | 0.874     | 22.2      |
|         | Space Between Flange | W1     | 0.661     | 16.8      |
| Hub     | Outer Diameter       | N      | 4.016     | 102.0     |
|         | Arbor Hole Diameter  | C      | 0.512     | 13.0      |
|         | Key Slit Width       | B      | 0.079     | 2.0       |
|         | Key Slit Diameter    | D      | 0.787     | 20.0      |

## Tape and Reel Information – Tape Length and Label Placement



### Notes:

1. Empty part cavities at the trailing and leading ends are sealed with cover tape. See EIA 481-1-A.
2. Labels are placed on the flange opposite the sprockets in the carrier tape.

### Handling Precautions

| Parameter                        | Rating   | Standard                        |
|----------------------------------|----------|---------------------------------|
| ESD – Human Body Model (HBM)     | Class 1A | ANSI/ESDA/JEDEC Standard JS-001 |
| ESD – Charged Device Model (CDM) | Class C3 | ANSI/ESDA/JEDEC Standard JS-002 |
| MSL – 260°C Convection Reflow    | MSL3     | IPC/JEDEC Standard J-STD-020    |



### Solderability

Compatible with both lead-free (260°C maximum reflow temperature) soldering processes. Package lead plating is NiPdAu. Au thickness is 0.095 µm.

### RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Product uses RoHS Exemption 7c-I to meet RoHS Compliance requirements.
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- PFOS Free
- SVHC Free

### Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations, and information about Qorvo:

Web: [www.qorvo.com](http://www.qorvo.com) Tel: 1-844-890-8163  
Email: [info-sales@qorvo.com](mailto:info-sales@qorvo.com)

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Email: [BTSApplications@qorvo.com](mailto:BTSApplications@qorvo.com)

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